

NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

Q0PACK Module

The NXH80T120L2Q0S2/P2G is a power module containing a T-type neutral point clamped (NPC) three level inverter stage. The integrated field stop trench IGBTs and fast recovery diodes provide lower conduction losses and switching losses, enabling designers to achieve high efficiency and superior reliability.

Features

- Low Switching Loss
- Low V_{CESAT}
- Compact 65.9 mm x 32.5 mm x 12 mm Package
- Thermistor
- Options with pre-applied thermal interface material (TIM) and without pre-applied TIM
- Options with solderable pins and press-fit pins

Typical Applications

- Solar Inverter
- Uninterruptable Power Supplies

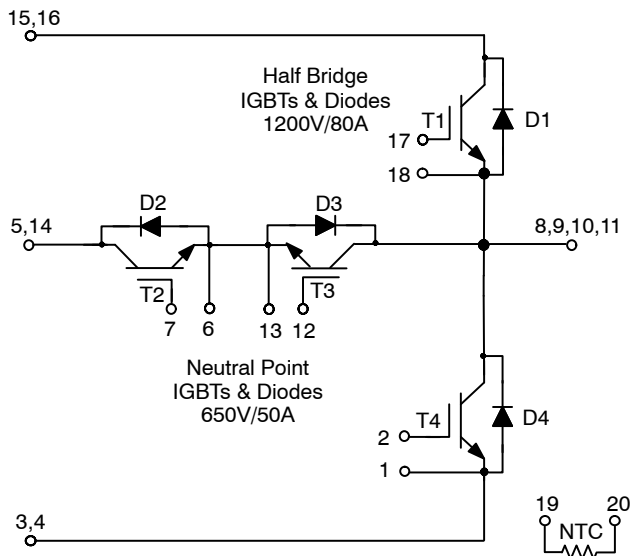
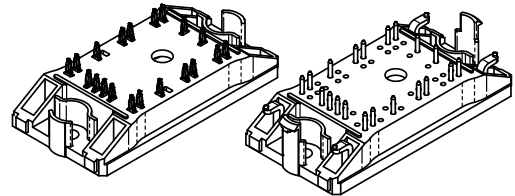


Figure 1. Schematic Diagram



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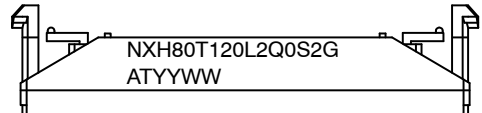
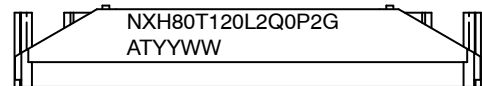
www.onsemi.com



Q0PACK
CASE 180AA
PRESS-FIT PINS

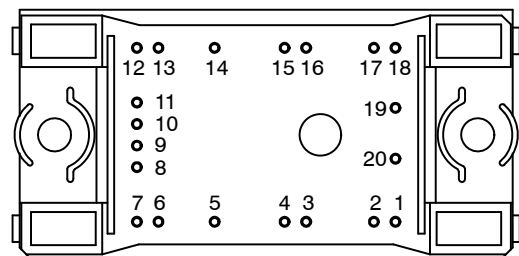
Q0PACK
CASE 180AB
SOLDERABLE PINS

MARKING DIAGRAMS



NXH80T120L2Q0S2G = Specific Device Code
G = Pb-free Package
A = Assembly Site Code
T = Test Site Code
YYWW = Year and Work Week Code

PIN ASSIGNMENTS



ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 13 of this data sheet.

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Table 1. MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|--------------|------------|------------------|
| HALF BRIDGE IGBT | | | |
| Collector–Emitter Voltage | V_{CES} | 1200 | V |
| Gate–Emitter Voltage | V_{GE} | ± 20 | V |
| Continuous Collector Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_C | 67 | A |
| Pulsed Collector Current ($T_J = 175^\circ\text{C}$) | I_{Cpulse} | 201 | A |
| Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 158 | W |
| Short Circuit Withstand Time @ $V_{GE} = 15\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J \leq 150^\circ\text{C}$ | T_{sc} | 5 | μs |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |
| NEUTRAL POINT IGBT | | | |
| Collector–Emitter Voltage | V_{CES} | 600 | V |
| Gate–Emitter Voltage | V_{GE} | ± 20 | V |
| Continuous Collector Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_C | 49 | A |
| Pulsed Collector Current ($T_J = 175^\circ\text{C}$) | I_{Cpulse} | 147 | A |
| Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 86 | W |
| Short Circuit Withstand Time @ $V_{GE} = 15\text{ V}$, $V_{CE} = 400\text{ V}$, $T_J \leq 150^\circ\text{C}$ | T_{sc} | 5 | μs |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |
| HALF BRIDGE DIODE | | | |
| Peak Repetitive Reverse Voltage | V_{RRM} | 1200 | V |
| Continuous Forward Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_F | 28 | A |
| Repetitive Peak Forward Current ($T_J = 175^\circ\text{C}$, t_p limited by T_{Jmax}) | I_{FRM} | 84 | A |
| Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 73 | W |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |
| NEUTRAL POINT DIODE | | | |
| Peak Repetitive Reverse Voltage | V_{RRM} | 650 | V |
| Continuous Forward Current @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | I_F | 33 | A |
| Repetitive Peak Forward Current ($T_J = 175^\circ\text{C}$, t_p limited by T_{Jmax}) | I_{FRM} | 99 | A |
| Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | P_{tot} | 63 | W |
| Minimum Operating Junction Temperature | T_{JMIN} | -40 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature | T_{JMAX} | 150 | $^\circ\text{C}$ |
| THERMAL PROPERTIES | | | |
| Storage Temperature range | T_{stg} | -40 to 125 | $^\circ\text{C}$ |
| INSULATION PROPERTIES | | | |
| Isolation test voltage, $t = 1\text{ sec}$, 60 Hz | V_{is} | 3000 | V_{RMS} |
| Creepage distance | | 12.7 | mm |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

Table 2. RECOMMENDED OPERATING RANGES

| Rating | Symbol | Min | Max | Unit |
|---------------------------------------|--------|-----|-----|------------------|
| Module Operating Junction Temperature | T_J | -40 | 150 | $^\circ\text{C}$ |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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Table 3. ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit | |
|---|--|---------------|-----|-------|------|--------------------|---------------|
| HALF BRIDGE IGBT CHARACTERISTICS | | | | | | | |
| Collector–Emitter Cutoff Current | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ | I_{CES} | – | – | 300 | μA | |
| Collector–Emitter Saturation Voltage | $V_{GE} = 15\text{ V}, I_C = 80\text{ A}, T_J = 25^\circ\text{C}$ | $V_{CE(sat)}$ | – | 2.05 | 2.85 | V | |
| | $V_{GE} = 15\text{ V}, I_C = 80\text{ A}, T_J = 150^\circ\text{C}$ | | – | 2.10 | – | | |
| Gate–Emitter Threshold Voltage | $V_{GE} = V_{CE}, I_C = 1.5\text{ mA}$ | $V_{GE(TH)}$ | – | 5.45 | 6.4 | V | |
| Gate Leakage Current | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | – | – | 300 | nA | |
| Turn-on Delay Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | $t_{d(on)}$ | – | 61 | – | ns | |
| Rise Time | | t_r | – | 28 | – | | |
| Turn-off Delay Time | | $t_{d(off)}$ | – | 205 | – | | |
| Fall Time | | t_f | – | 41 | – | | |
| Turn-on Switching Loss per Pulse | | E_{on} | – | 550 | – | | μJ |
| Turn off Switching Loss per Pulse | | E_{off} | – | 1100 | – | | |
| Turn-on Delay Time | $T_J = 125^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | $t_{d(on)}$ | – | 58 | – | ns | |
| Rise Time | | t_r | – | 30 | – | | |
| Turn-off Delay Time | | $t_{d(off)}$ | – | 230 | – | | |
| Fall Time | | t_f | – | 63 | – | | |
| Turn-on Switching Loss per Pulse | | E_{on} | – | 720 | – | | μJ |
| Turn off Switching Loss per Pulse | | E_{off} | – | 1700 | – | | |
| Input Capacitance | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 10\text{ kHz}$ | C_{ies} | – | 19400 | – | pF | |
| Output Capacitance | | C_{oes} | – | 400 | – | | |
| Reverse Transfer Capacitance | | C_{res} | – | 340 | – | | |
| Total Gate Charge | $V_{CE} = 600\text{ V}, I_C = 80\text{ A}, V_{GE} = +15\text{ V}$ | Q_g | – | 800 | – | nC | |
| Thermal Resistance – chip-to–heatsink | Thermal grease, Thickness = $76\ \mu\text{m} \pm 2\%$, $\lambda = 2.9\text{ W/mK}$ | R_{thJH} | – | 0.60 | – | $^\circ\text{C/W}$ | |

NEUTRAL POINT DIODE CHARACTERISTICS

| | | | | | | |
|---------------------------------------|---|--|------------|------|------|------------------------|
| Diode Forward Voltage | $I_F = 60\text{ A}, T_J = 25^\circ\text{C}$ | V_F | – | 1.7 | 2.2 | V |
| | $I_F = 60\text{ A}, T_J = 150^\circ\text{C}$ | | – | 1.6 | – | |
| Reverse Recovery Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | t_{rr} | – | 39 | – | ns |
| Reverse Recovery Charge | | Q_{rr} | – | 1.1 | – | μC |
| Peak Reverse Recovery Current | | I_{RRM} | – | 48 | – | A |
| Peak Rate of Fall of Recovery Current | | di/dt | – | 3400 | – | $\text{A}/\mu\text{s}$ |
| Reverse Recovery Energy | | E_{rr} | – | 400 | – | μJ |
| Reverse Recovery Time | | $T_J = 125^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | t_{rr} | – | 78 | – |
| Reverse Recovery Charge | Q_{rr} | | – | 2.0 | – | μC |
| Peak Reverse Recovery Current | I_{RRM} | | – | 59 | – | A |
| Peak Rate of Fall of Recovery Current | di/dt | | – | 1600 | – | $\text{A}/\mu\text{s}$ |
| Reverse Recovery Energy | E_{rr} | | – | 550 | – | μJ |
| Thermal Resistance – chip-to–heatsink | Thermal grease, Thickness = $76\ \mu\text{m} \pm 2\%$, $\lambda = 2.9\text{ W/mK}$ | | R_{thJH} | – | 1.50 | – |

NEUTRAL POINT IGBT CHARACTERISTICS

| | | | | | | |
|--------------------------------------|--|---------------|---|------|------|---------------|
| Collector–Emitter Cutoff Current | $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$ | I_{CES} | – | – | 250 | μA |
| Collector–Emitter Saturation Voltage | $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 25^\circ\text{C}$ | $V_{CE(sat)}$ | – | 1.40 | 1.75 | V |
| | $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 150^\circ\text{C}$ | | – | 1.50 | – | |
| Gate–Emitter Threshold Voltage | $V_{GE} = V_{CE}, I_C = 1.2\text{ mA}$ | $V_{GE(TH)}$ | – | 5.45 | 6.4 | V |
| Gate Leakage Current | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | – | – | 200 | nA |

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Table 3. ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|---|--|--------------|-----|------|-----|--------------------|
| NEUTRAL POINT IGBT CHARACTERISTICS | | | | | | |
| Turn-on Delay Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | $t_{d(on)}$ | – | 30 | – | ns |
| Rise Time | | t_r | – | 19 | – | |
| Turn-off Delay Time | | $t_{d(off)}$ | – | 110 | – | |
| Fall Time | | t_f | – | 23 | – | |
| Turn-on Switching Loss per Pulse | | E_{on} | – | 800 | – | μJ |
| Turn off Switching Loss per Pulse | | E_{off} | – | 480 | – | |
| Turn-on Delay Time | $T_J = 125^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | $t_{d(on)}$ | – | 32 | – | ns |
| Rise Time | | t_r | – | 18 | – | |
| Turn-off Delay Time | | $t_{d(off)}$ | – | 120 | – | |
| Fall Time | | t_f | – | 35 | – | |
| Turn-on Switching Loss per Pulse | | E_{on} | – | 1100 | – | μJ |
| Turn off Switching Loss per Pulse | | E_{off} | – | 880 | – | |
| Input Capacitance | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 10\text{ kHz}$ | C_{ies} | – | 9400 | – | pF |
| Output Capacitance | | C_{oes} | – | 280 | – | |
| Reverse Transfer Capacitance | | C_{res} | – | 250 | – | |
| Total Gate Charge | $V_{CE} = 480\text{ V}, I_C = 50\text{ A}, V_{GE} = +15\text{ V}$ | Q_g | – | 395 | – | nC |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = $76\ \mu\text{m} \pm 2\%$, $\lambda = 2.9\text{ W/mK}$ | R_{thJH} | – | 1.10 | – | $^\circ\text{C/W}$ |

HALF BRIDGE DIODE CHARACTERISTICS

| | | | | | | |
|---------------------------------------|---|--|------------|------|------|------------------------|
| Diode Forward Voltage | $I_F = 40\text{ A}, T_J = 25^\circ\text{C}$ | V_F | – | 2.11 | 3.10 | V |
| | $I_F = 40\text{ A}, T_J = 150^\circ\text{C}$ | | – | 1.50 | – | |
| Reverse recovery time | $T_J = 25^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | t_{rr} | – | 45 | – | ns |
| Reverse recovery charge | | Q_{rr} | – | 2.7 | – | μC |
| Peak reverse recovery current | | I_{RRM} | – | 110 | – | A |
| Peak rate of fall of recovery current | | di/dt | – | 7100 | – | $\text{A}/\mu\text{s}$ |
| Reverse recovery energy | | E_{rr} | – | 1000 | – | μJ |
| Reverse recovery time | | $T_J = 125^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 60\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4.7\ \Omega$ | t_{rr} | – | 185 | – |
| Reverse recovery charge | Q_{rr} | | – | 6 | – | μC |
| Peak reverse recovery current | I_{RRM} | | – | 150 | – | A |
| Peak rate of fall of recovery current | di/dt | | – | 5900 | – | $\text{A}/\mu\text{s}$ |
| Reverse recovery energy | E_{rr} | | – | 1900 | – | μJ |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = $76\ \mu\text{m} \pm 2\%$, $\lambda = 2.9\text{ W/mK}$ | | R_{thJH} | – | 1.30 | – |

THERMISTOR CHARACTERISTICS

| | | | | | | |
|----------------------------|--------------------------------|--------------|----|------|---|------------|
| Nominal resistance | $T = 25^\circ\text{C}$ | R_{25} | – | 22 | – | k Ω |
| Nominal resistance | $T = 100^\circ\text{C}$ | R_{100} | – | 1486 | – | Ω |
| Deviation of R25 | | $\Delta R/R$ | –5 | – | 5 | % |
| Power dissipation | | P_D | – | 200 | – | mW |
| Power dissipation constant | | | – | 2 | – | mW/K |
| B-value | B(25/50), tolerance $\pm 3\%$ | | – | 3950 | – | K |
| B-value | B(25/100), tolerance $\pm 3\%$ | | – | 3998 | – | K |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS – Half Bridge IGBT and Neutral Point Diode

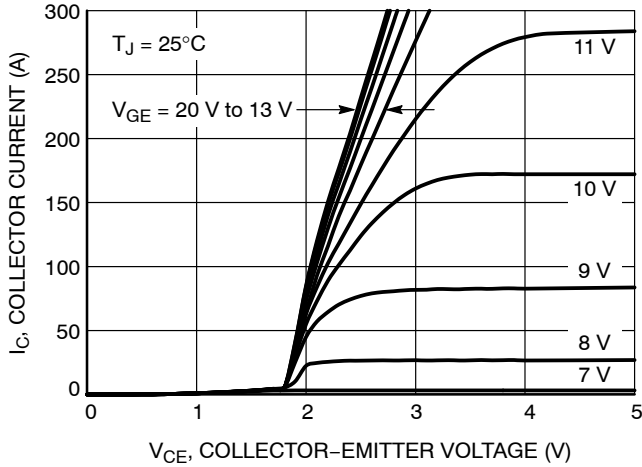


Figure 2. Typical Output Characteristics

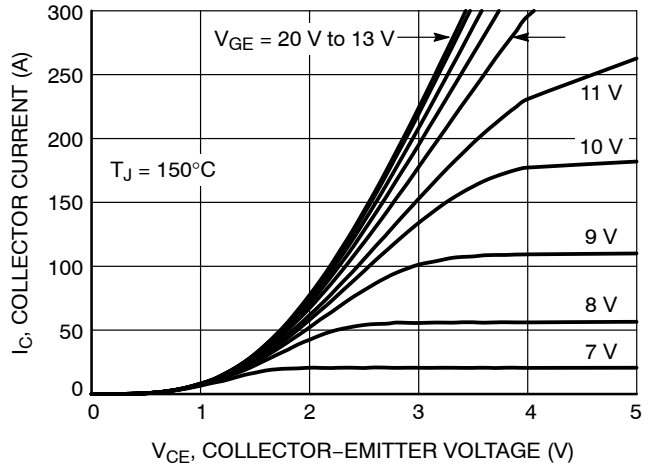


Figure 3. Typical Output Characteristics

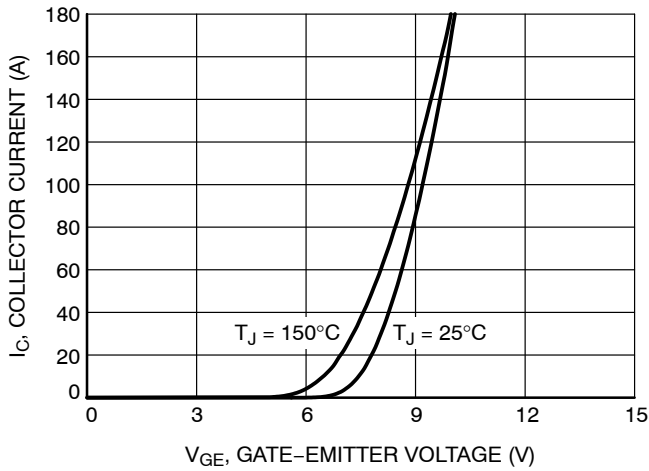


Figure 4. Typical Transfer Characteristics

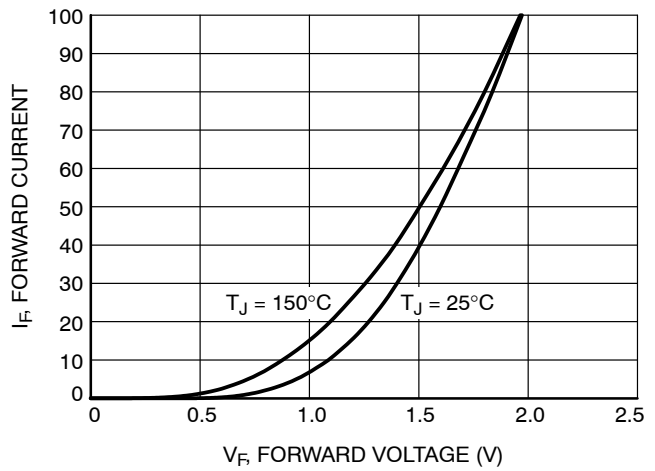


Figure 5. Diode Forward Characteristics

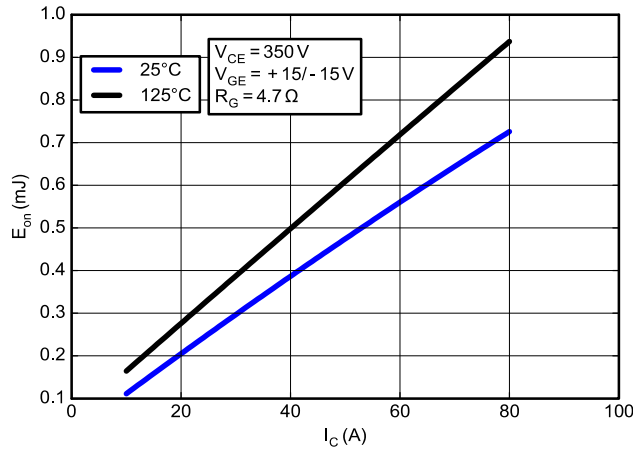


Figure 6. Typical Turn On Loss vs. IC

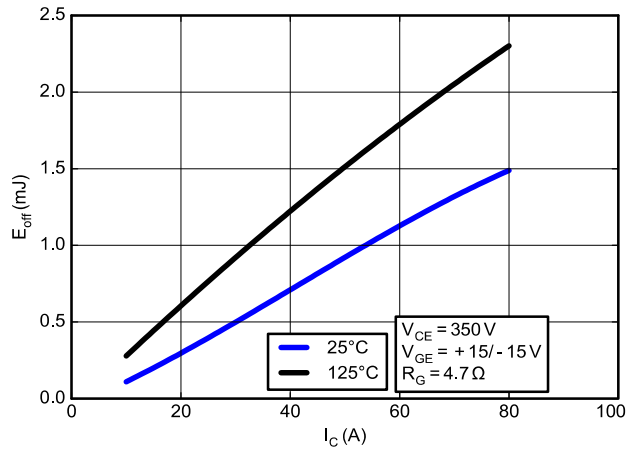


Figure 7. Typical Turn Off Loss vs. IC

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TYPICAL CHARACTERISTICS – Half Bridge IGBT and Neutral Point Diode

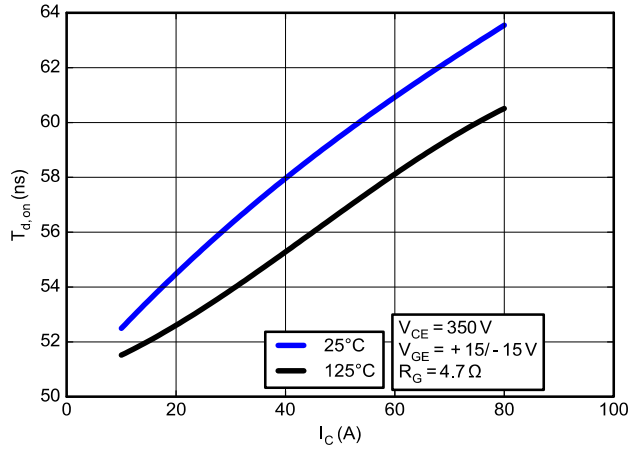


Figure 8. Typical On Switching Times vs. IC

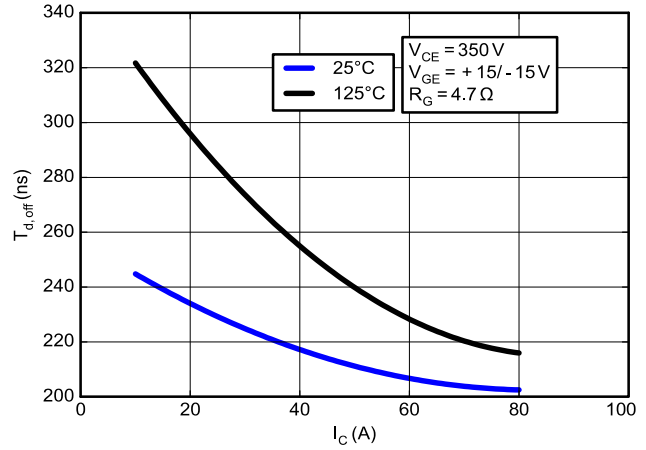


Figure 9. Typical Off Switching Times vs. IC

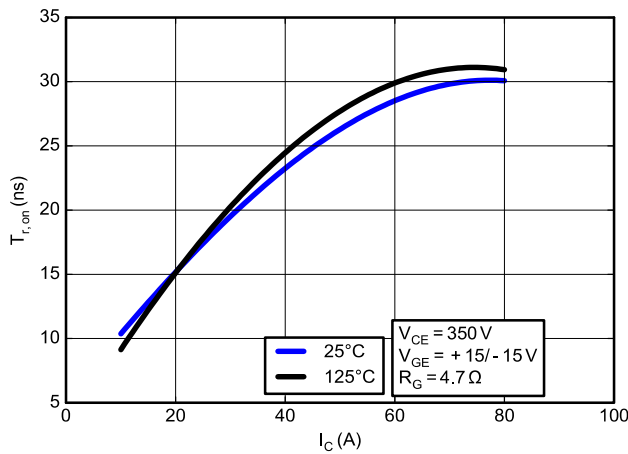


Figure 10. Typical On Rise Times vs. IC

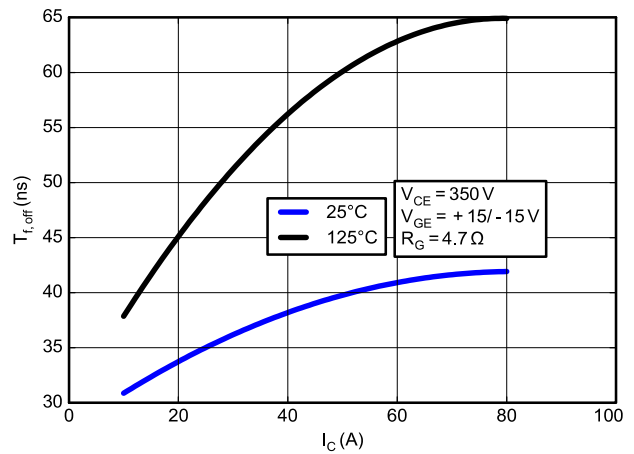


Figure 11. Typical Off Fall Times vs. IC

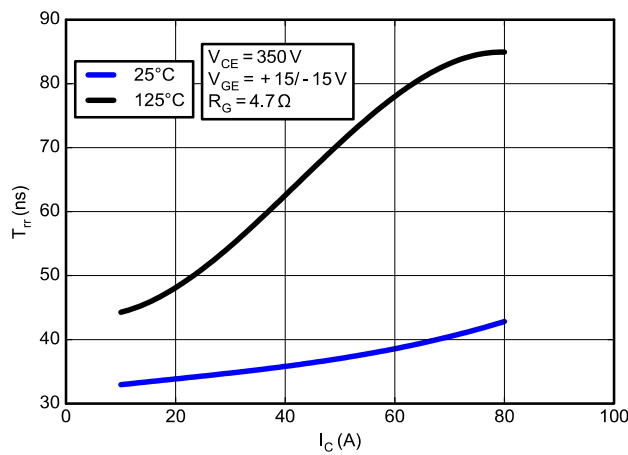


Figure 12. Typical Reverse Recovery Time vs. IC

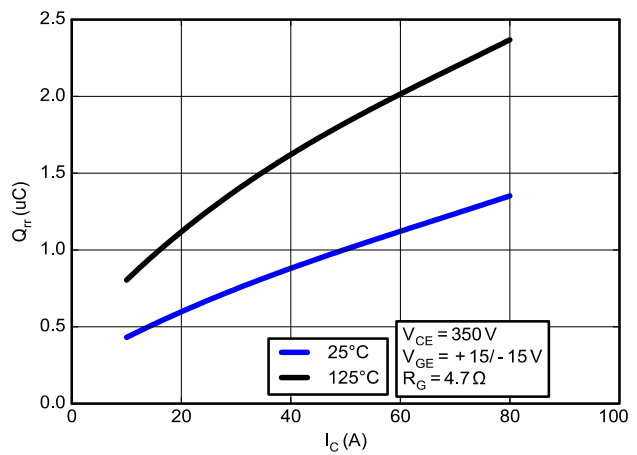


Figure 13. Typical Reverse Recovery Charge vs. IC

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TYPICAL CHARACTERISTICS – Half Bridge IGBT and Neutral Point Diode

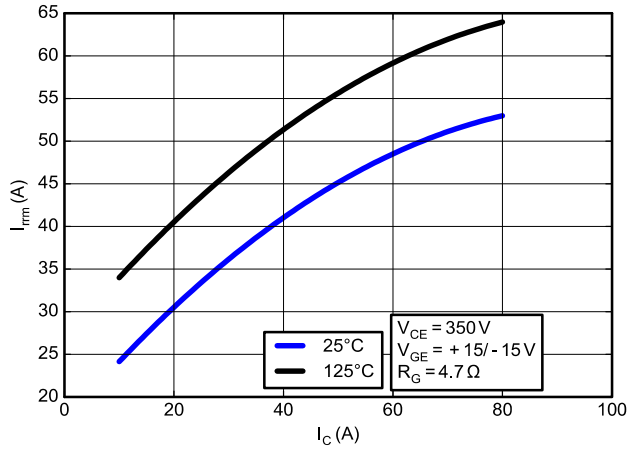


Figure 14. Typical Reverse Recovery Peak Current vs. I_C

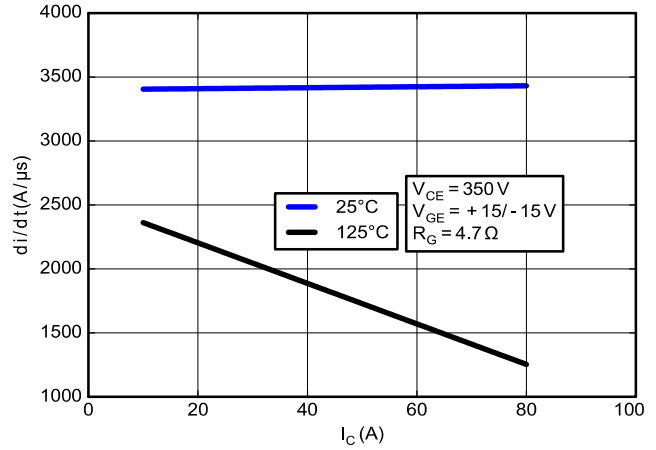


Figure 15. Typical Diode Current Slope vs. I_C

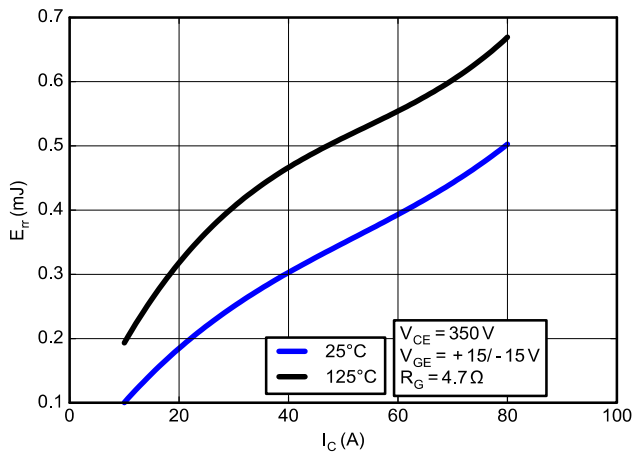


Figure 16. Typical Reverse Recovery Energy vs. I_C

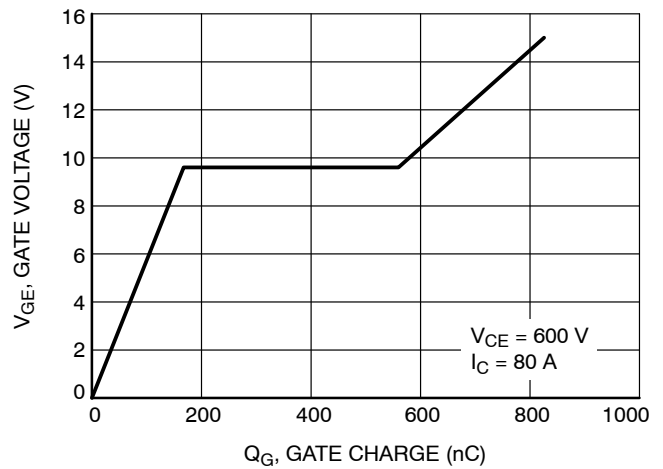


Figure 17. Gate Voltage vs. Gate Charge

NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

TYPICAL CHARACTERISTICS – Half Bridge IGBT and Neutral Point Diode

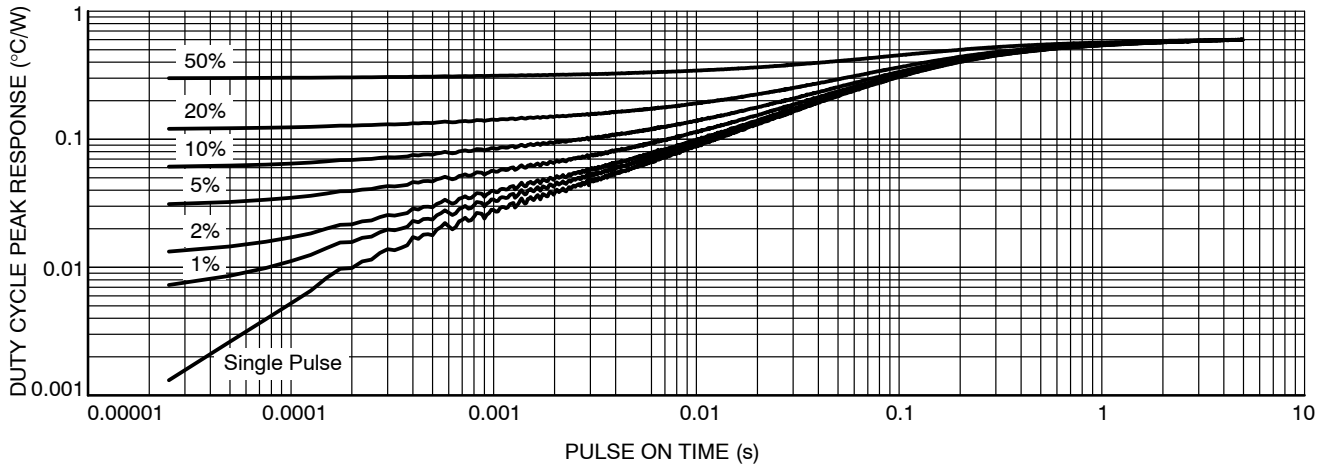


Figure 18. IGBT Transient Thermal Impedance

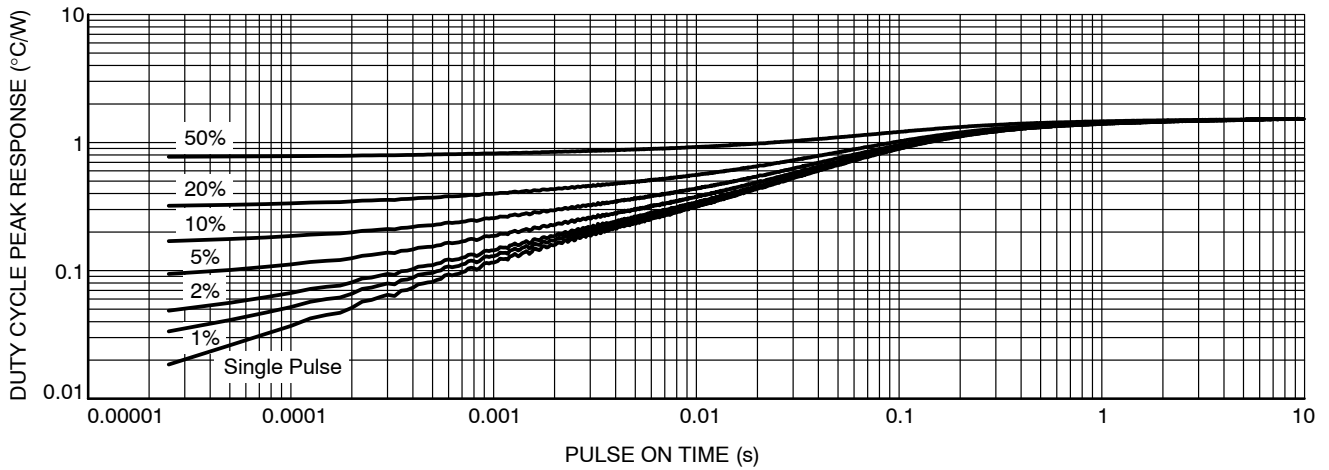


Figure 19. Diode Transient Thermal Impedance

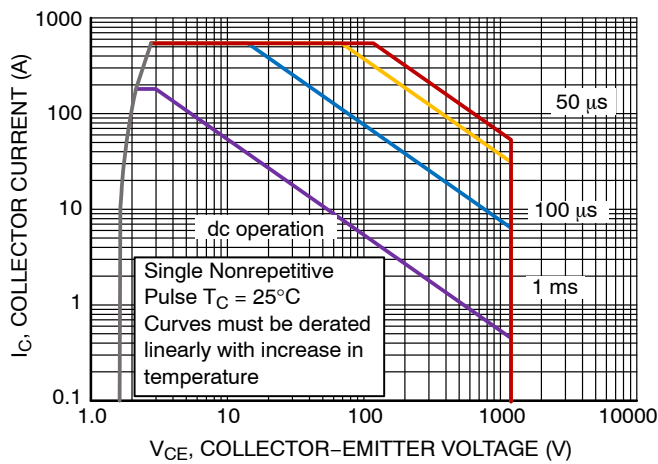


Figure 20. T1 & T4 FBSOA

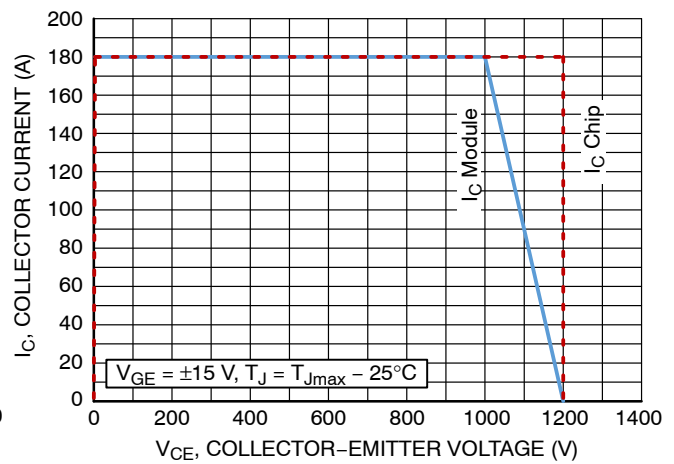


Figure 21. T1 & T4 RBSOA

NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

TYPICAL CHARACTERISTICS – Neutral Point IGBT and Half Bridge Diode

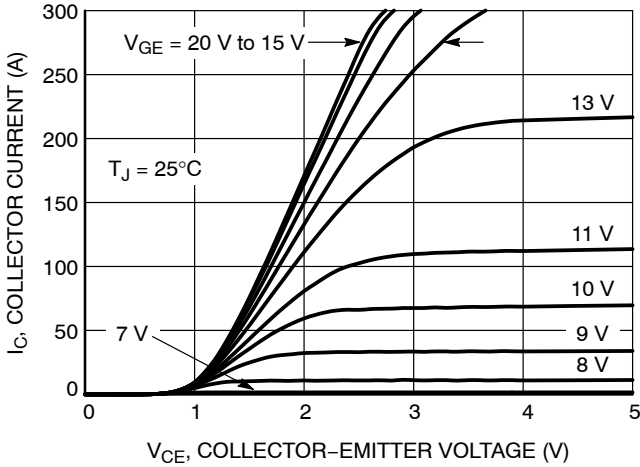


Figure 22. Typical Output Characteristics

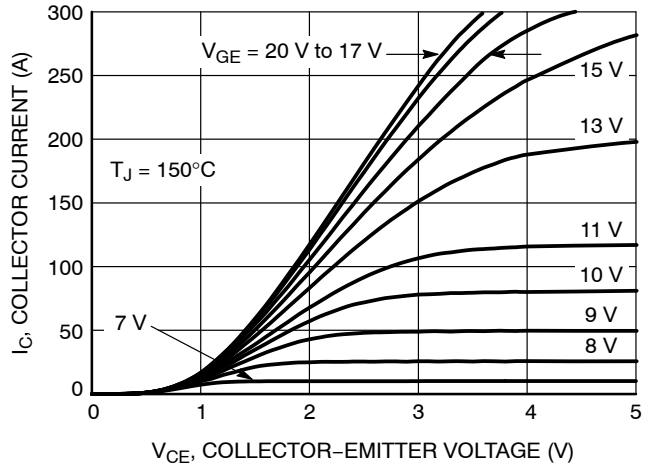


Figure 23. Typical Output Characteristics

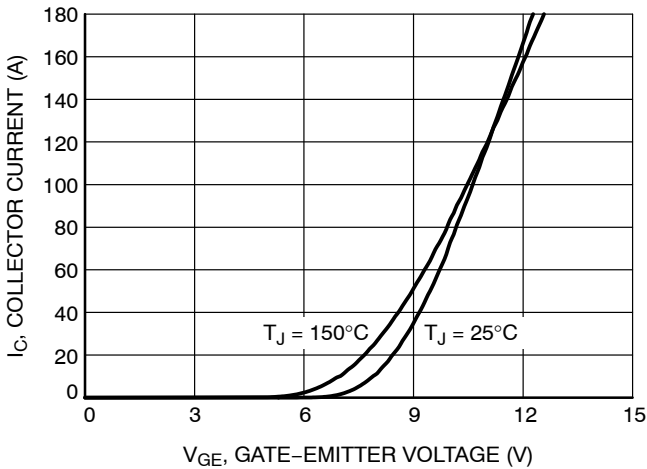


Figure 24. Typical Transfer Characteristics

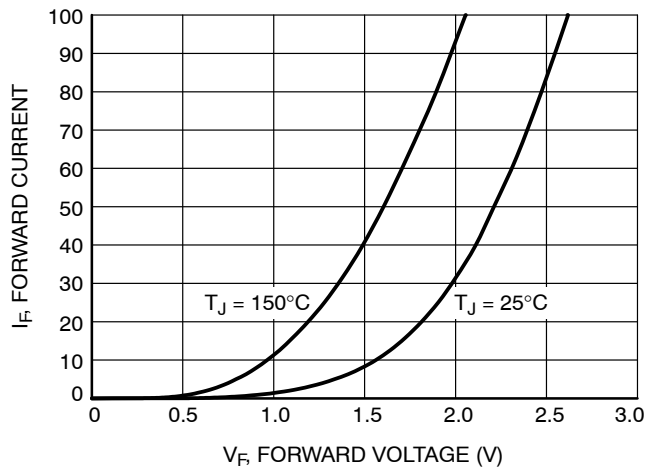


Figure 25. Diode Forward Characteristics

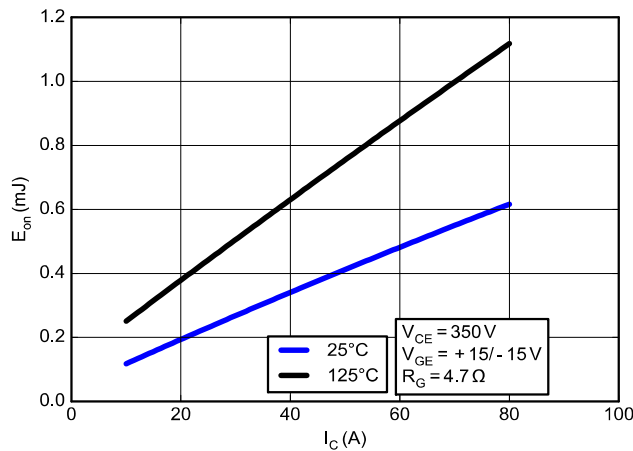


Figure 26. Typical Turn On Loss vs. IC

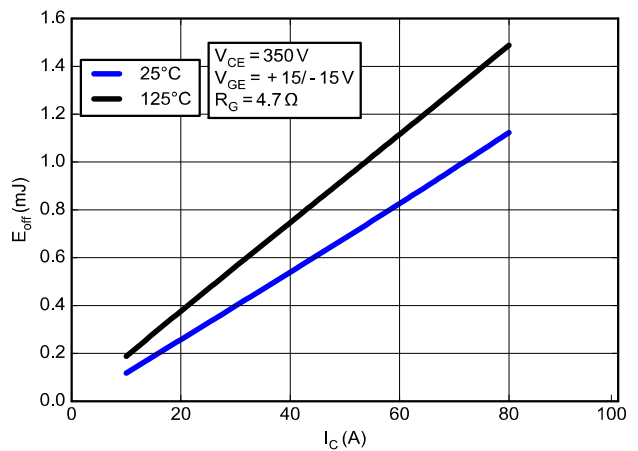


Figure 27. Typical Turn Off Loss vs. IC

NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

TYPICAL CHARACTERISTICS – Neutral Point IGBT and Half Bridge Diode

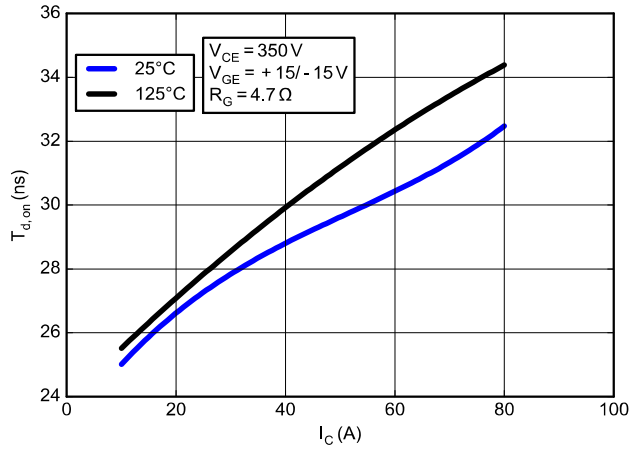


Figure 28. Typical On Switching Times vs. IC

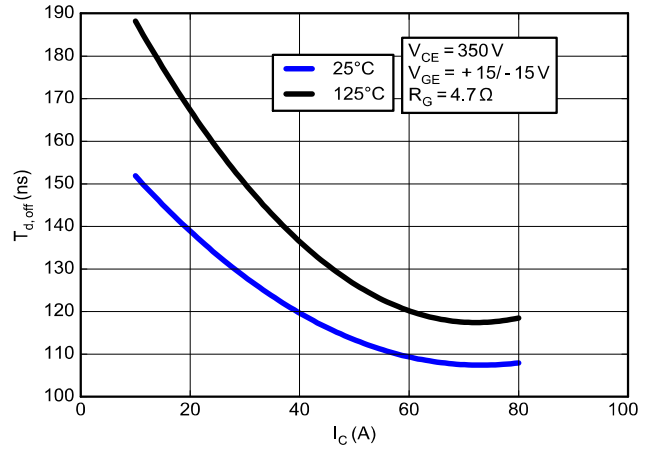


Figure 29. Typical Off Switching Times vs. IC

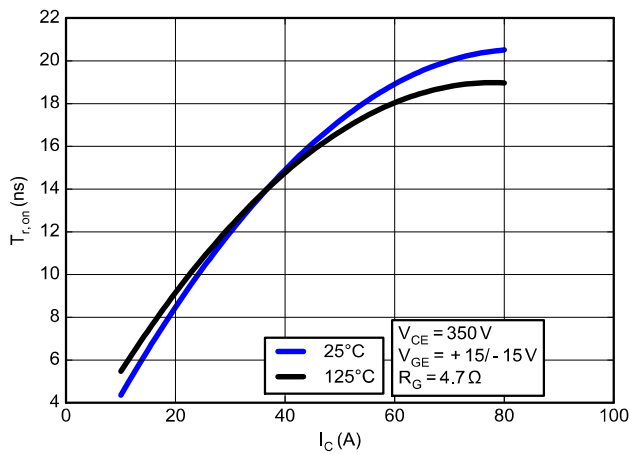


Figure 30. Typical On Rise Times vs. IC

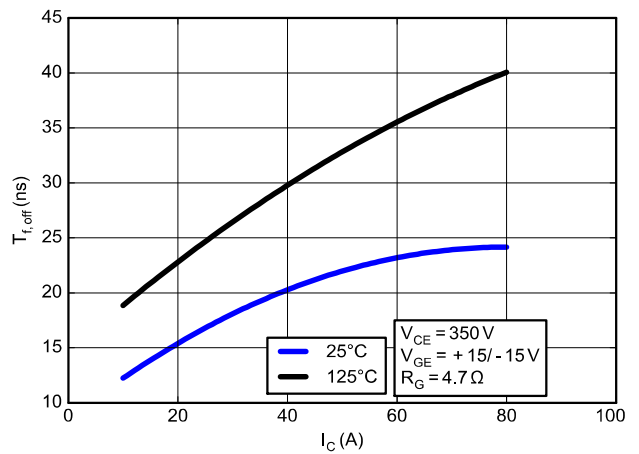


Figure 31. Typical Off Fall Times vs. IC

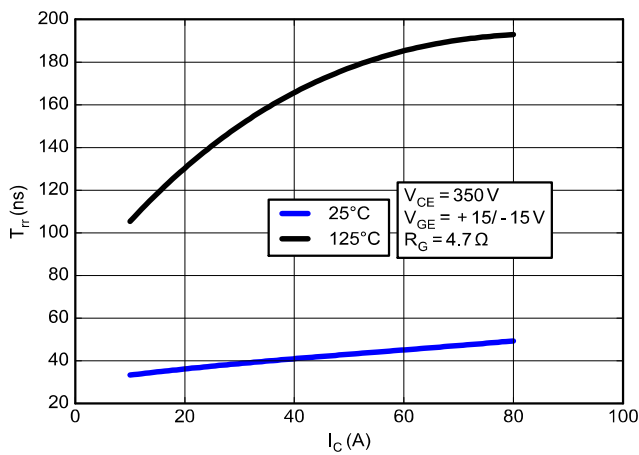


Figure 32. Typical Reverse Recovery Time vs. IC

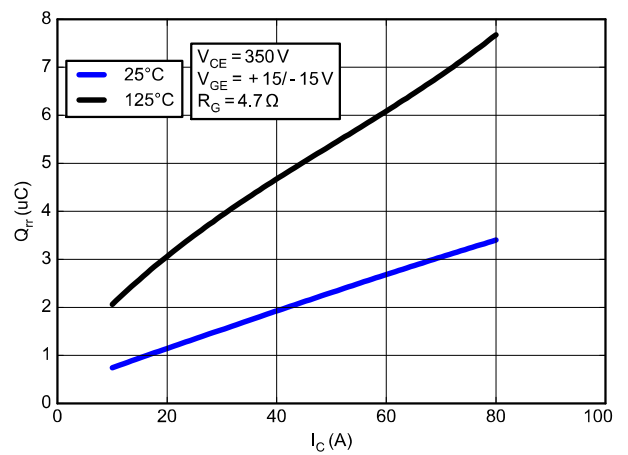


Figure 33. Typical Reverse Recovery Charge vs. IC

TYPICAL CHARACTERISTICS – Neutral Point IGBT and Half Bridge Diode

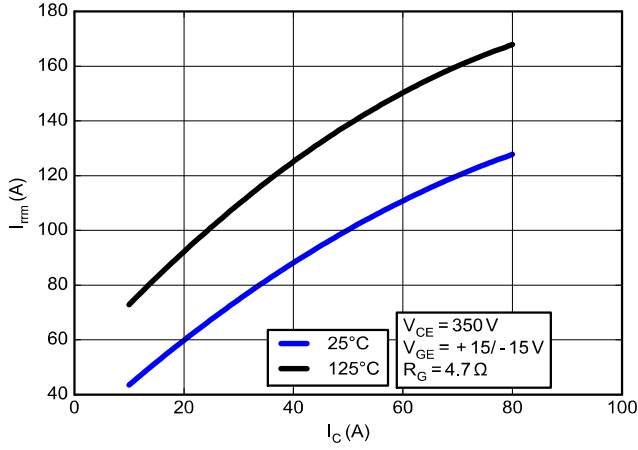


Figure 34. Typical Reverse Recovery Peak Current vs. I_C

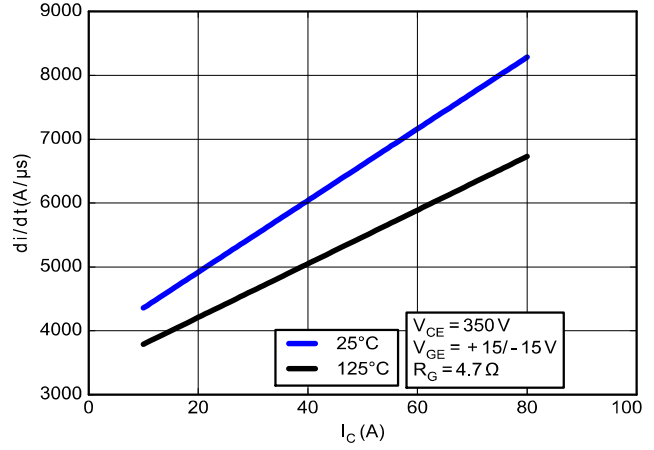


Figure 35. Typical Diode Current Slope vs. I_C

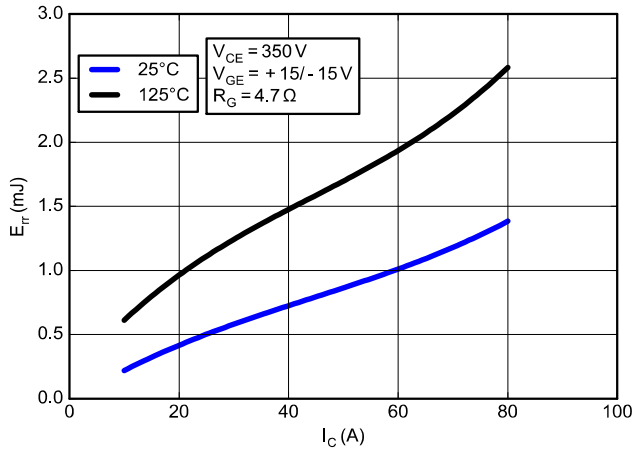


Figure 36. Typical Reverse Recovery Energy vs. I_C

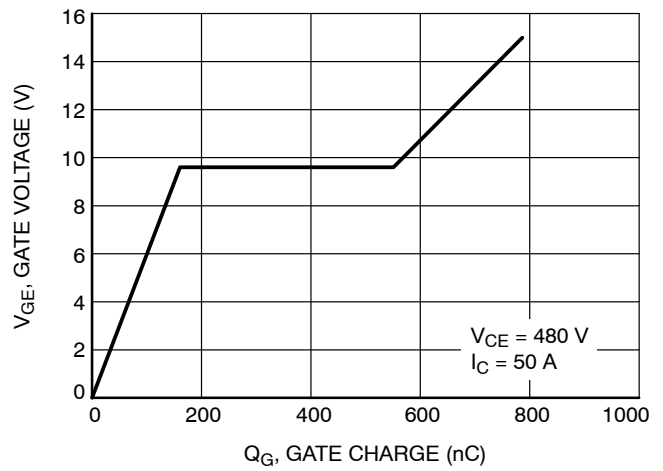


Figure 37. Gate Voltage vs. Gate Charge

NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

TYPICAL CHARACTERISTICS – Neutral Point IGBT and Half Bridge Diode

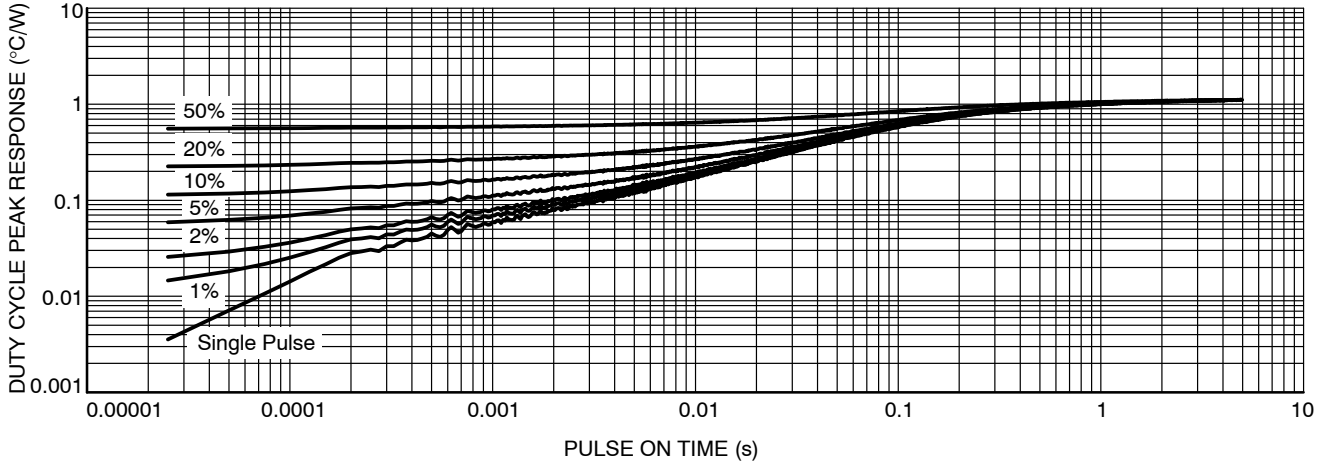


Figure 38. IGBT Transient Thermal Impedance

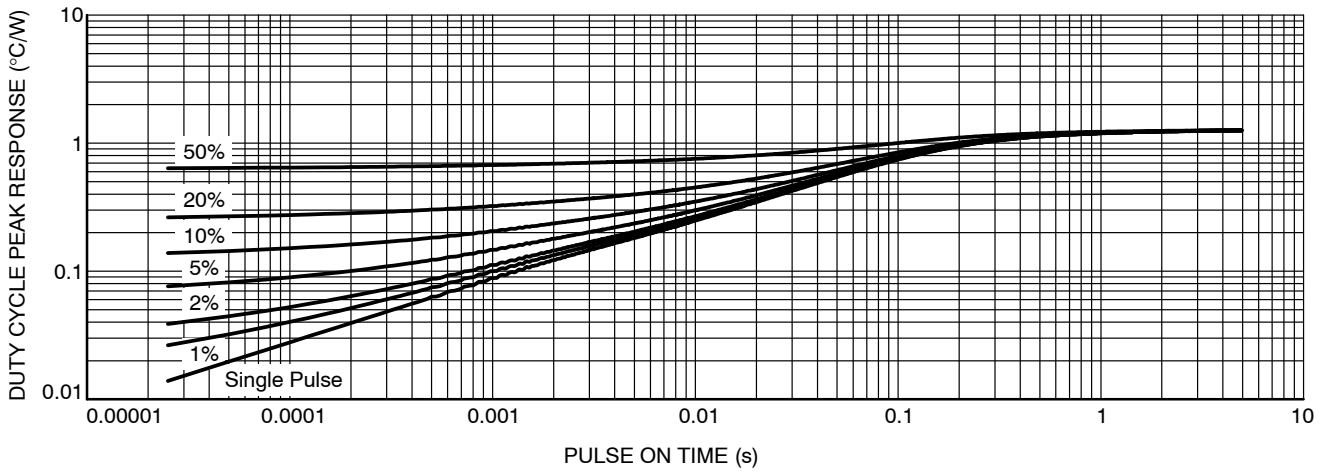


Figure 39. Diode Transient Thermal Impedance

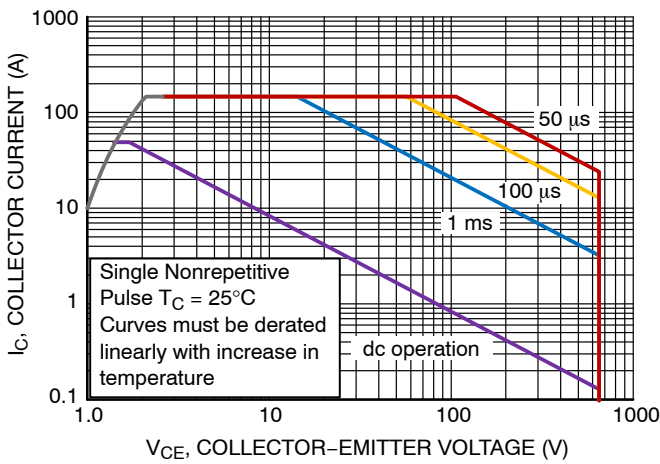


Figure 40. T2 & T3 FBSOA

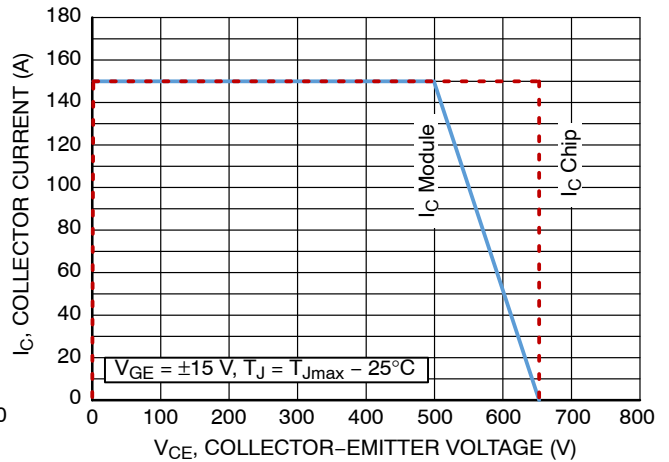


Figure 41. T2 & T3 RBSOA

NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

TYPICAL CHARACTERISTICS – Thermistor

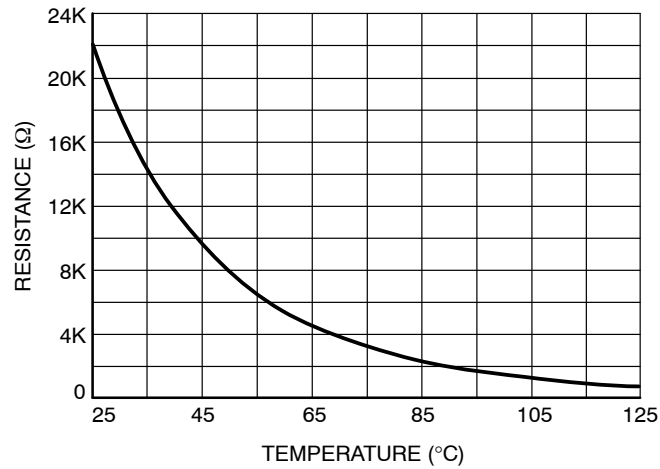


Figure 42. Thermistor Characteristics

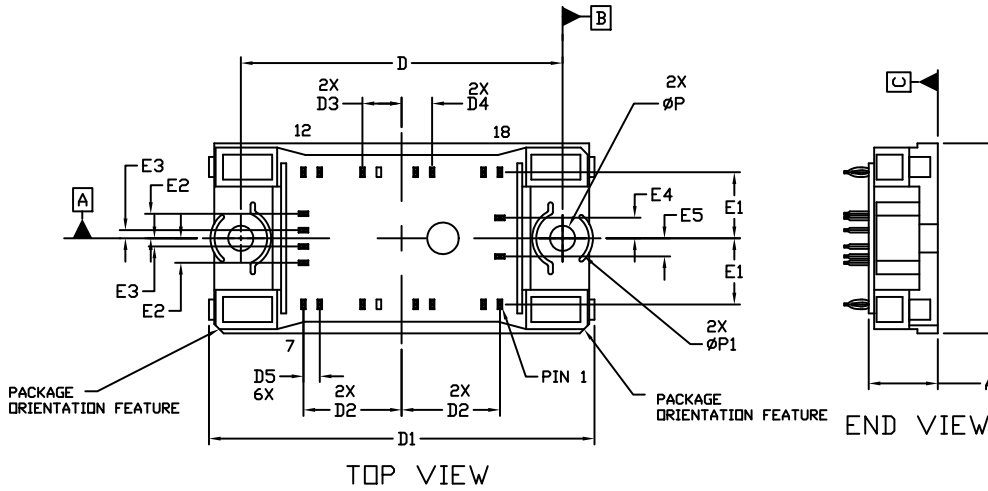
ORDERING INFORMATION

| Orderable Part Number | Marking | Package | Shipping |
|-----------------------|-------------------|--|-------------------------|
| NXH80T120L2Q0P2G | NXH80T120L2Q0P2G | Q0PACK – Case 180AA (Pb-Free and Halide-Free) | 24 Units / Blister Tray |
| NXH80T120L2Q0S2G | NXH80T120L2Q0S2G | Q0PACK – Case 180AB (Pb-Free and Halide-Free) | 24 Units / Blister Tray |
| NXH80T120L2Q0S2TG | NXH80T120L2Q0S2TG | Q0PACK – Case 180AB with pre-applied thermal interface material (TIM) (Pb-Free and Halide-Free) | 24 Units / Blister Tray |

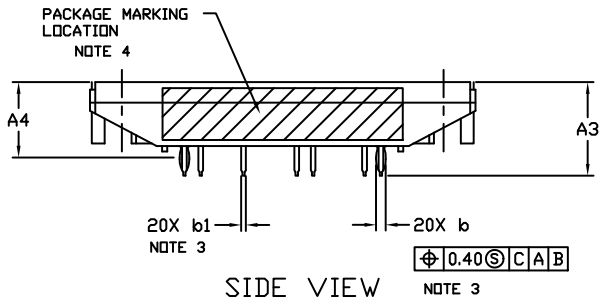
NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AA
ISSUE D

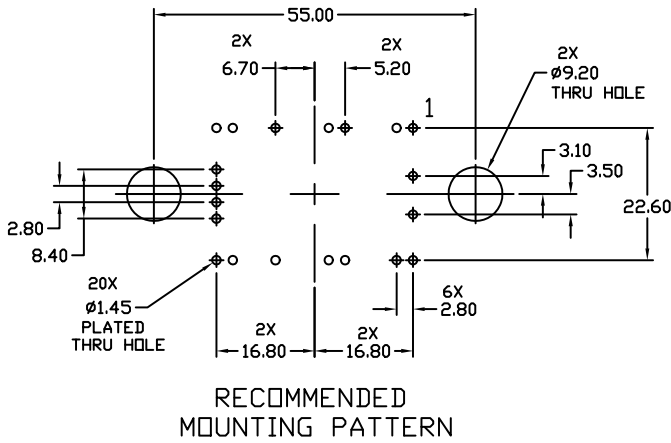


| DIM | MILLIMETERS | | |
|-----|-------------|-------|-------|
| | MIN. | NOM. | MAX. |
| A | 11.33 | 11.83 | 12.33 |
| A3 | 15.50 | 16.00 | 16.50 |
| A4 | 12.88 BSC | | |
| b | 1.61 | 1.66 | 1.71 |
| b1 | 0.75 | 0.80 | 0.85 |
| D | 54.80 | 55.00 | 55.20 |
| D1 | 65.70 | 67.90 | 70.10 |
| D2 | 16.80 BSC | | |
| D3 | 6.70 BSC | | |
| D4 | 5.20 BSC | | |
| D5 | 2.80 BSC | | |
| E | 32.30 | 32.50 | 32.70 |
| E1 | 11.30 BSC | | |
| E2 | 4.20 BSC | | |
| E3 | 1.40 BSC | | |
| E4 | 3.50 BSC | | |
| E5 | 3.10 BSC | | |
| P | 4.10 | 4.30 | 4.50 |
| P1 | 8.50 | 9.00 | 9.50 |



NOTES:

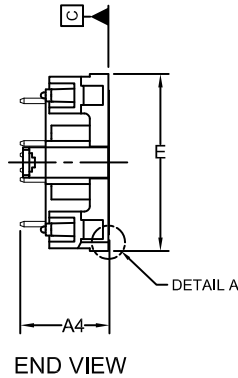
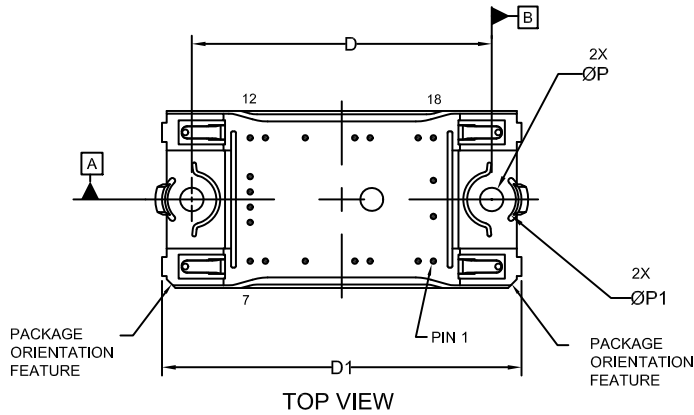
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A4.
4. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.



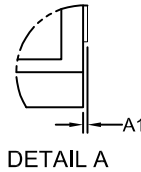
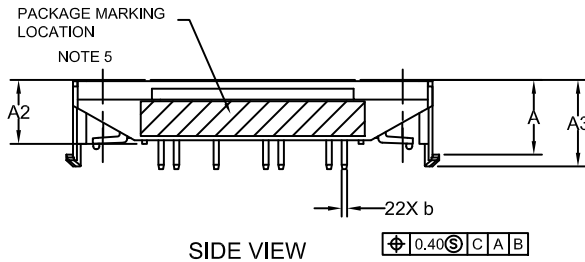
NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AB
ISSUE D



| DIM | MILLIMETERS | |
|-----|-------------|-------|
| | MIN. | NOM. |
| A | 13.50 | 13.90 |
| A1 | 0.10 | 0.30 |
| A2 | 11.50 | 11.90 |
| A3 | 15.65 | 16.05 |
| A4 | 16.35 REF | |
| b | 0.95 | 1.05 |
| D | 54.80 | 55.20 |
| D1 | 65.60 | 66.20 |
| E | 32.20 | 32.80 |
| P | 4.20 | 4.40 |
| P1 | 8.90 | 9.10 |



NOTE 4

| PIN | PIN POSITION | | PIN | PIN POSITION | |
|-----|--------------|--------|-----|--------------|-------|
| | X | Y | | X | Y |
| 1 | 16.80 | -11.30 | 11 | -16.80 | 4.20 |
| 2 | 14.00 | -11.30 | 12 | -16.80 | 11.30 |
| 3 | 5.20 | -11.30 | 13 | -14.00 | 11.30 |
| 4 | 2.40 | -11.30 | 14 | -6.70 | 11.30 |
| 5 | -6.70 | -11.30 | 15 | 2.40 | 11.30 |
| 6 | -14.00 | -11.30 | 16 | 5.20 | 11.30 |
| 7 | -16.80 | -11.30 | 17 | 14.00 | 11.30 |
| 8 | -16.80 | -4.20 | 18 | 16.80 | 11.30 |
| 9 | -16.80 | -1.40 | 19 | 16.80 | 3.50 |
| 10 | -16.80 | 1.40 | 20 | 16.80 | -3.10 |

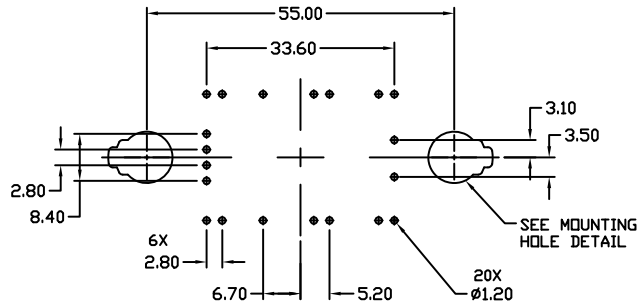
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 1.00 AND 3.00 FROM THE TERMINAL TIP.
- POSITION OF THE CENTER OF THE TERMINALS IS DETERMINED FROM DATUM B THE CENTER OF DIMENSION D, X DIRECTION, AND FROM DATUM A, Y DIRECTION. POSITIONAL TOLERANCE, AS NOTED IN DRAWING, APPLIES TO EACH TERMINAL IN BOTH DIRECTIONS.
- PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.

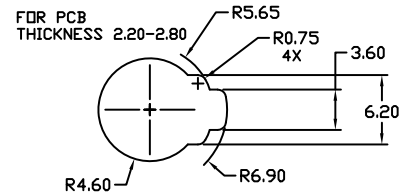
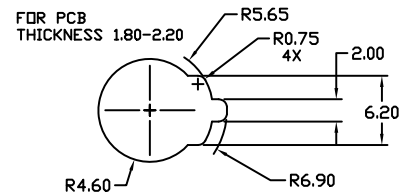
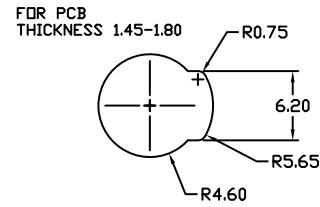
NXH80T120L2Q0S2G/S2TG, NXH80T120L2Q0P2G

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AB
ISSUE D



**RECOMMENDED
MOUNTING PATTERN**



MOUNTING HOLE DETAIL

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